

PLUS Search Results for S/N 09/451,619, Searched September 12, 2001 (Top 50)

4577215	4618876	4802137	5605853	5940705
5482879	4903097	5212541	5612237	5946240
5879992	5526307	5216268	5625213	5950087
6229176	5760435	5216269	5702965	5972753
5016068	6069381	5289026	5801993	6034892
5295107	6207989	5292681	5814543	6037226
6046086	6239465	5432109	5851880	6093607
4442447	4417264	5447877	5852312	6124168
4513397	4558339	5457061	5858840	6180977
4592130	4590665	5595920	5877525	6188102

**Most Frequently Occurring Classifications of Patents Returned  
From A Search of 09/451,619 on September 12, 2001**

**Combined Classifications**

12 257/315

12 257/316

10 438/264

9 257/321

9 438/266

7 257/314

6 365/185.18

5 257/317

5 365/185.14

5 438/258

4 257/319

4 365/185.29

4 365/185.33

4 438/257

4 438/265

3 257/320

3 365/185.01

3 365/185.06

3 365/185.1

3 365/185.16

3 365/185.27

3 365/185.28

3 438/201

3 438/267

2 257/318

2 257/324

2 257/330

2 365/185.3

2 365/185.31

2 438/211

2 438/261

2 438/263

2 438/286

2 438/297

2 438/588

2 438/593

2 438/594

**12 257/315 (2 OR, 10 XR)**

Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)  
257/315 ...With floating gate electrode

**12 257/316 (3 OR, 9 XR)**

Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)  
257/315 ...With floating gate electrode  
257/316 ....With additional contacted control electrode

**10 438/264 (6 OR, 4 XR)**

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS  
438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)  
438/257 ..Having additional gate electrode surrounded by dielectric (i.e., floating gate)  
438/264 ...Tunneling insulator

**9 257/321 (4 OR, 5 XR)**

Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)  
257/315 ...With floating gate electrode  
257/316 ....With additional contacted control electrode  
257/321 .....With thin insulator region for charging or discharging floating electrode by quantum mechanical tunneling

**9 438/266 (2 OR, 7 XR)**

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS  
438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)  
438/257 ..Having additional gate electrode surrounded by dielectric (i.e., floating gate)

- 438/266 ...Having additional, nonmemory control electrode or channel portion (e.g., for accessing field effect transistor structure, etc.)
- 7 257/314 (3 OR, 4 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)
- 6 365/185.18 (0 OR, 6 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing
- 5 257/317 (1 OR, 4 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)  
257/315 ...With floating gate electrode  
257/316 ....With additional contacted control electrode  
257/317 .....With irregularities on electrode to facilitate charging or discharging of floating electrode
- 5 365/185.14 (2 OR, 3 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.05 .Particular connection  
365/185.14 ..Program gate
- 5 438/258 (2 OR, 3 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS  
438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)  
438/257 ..Having additional gate electrode surrounded by dielectric (i.e., floating gate)  
438/258 ...Including additional field effect transistor (e.g., sense or access transistor, etc.)
- 4 257/319 (3 OR, 1 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)